

## **ABSTRACT OF THE DISCLOSURE**

A method of forming a fine pattern by a tri-layer resist process to overcome a bi-layer resist process is disclosed. When a fine pattern is formed using a silicon photoresist, a gas protection film is coated on a photoresist to prevent 5 exhaustion of silicon gas generated from the photoresist in light examination of high energy. As a result, lens of exposure equipment may be prevented from being contaminated.